

# Frontier Detectors for Frontier Physics

14<sup>th</sup> Pisa meeting on  
advanced detectors

La Biodola • Isola d'Elba • Italy  
27 May - 2 June, 2018



## High-energy $e^-/e^+$ spectrometer via coherent interaction in a bent crystal

E. Bagli<sup>1</sup>, V. Guidi<sup>1,2</sup>, A. Howard<sup>3</sup>

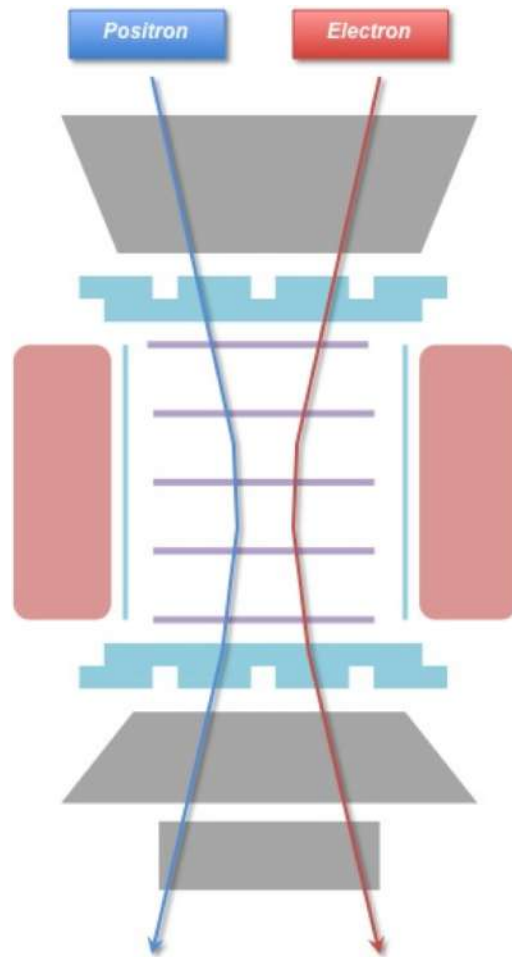
<sup>1</sup> INFN Sezione di Ferrara, Via Saragat 1, Ferrara, 44121, Italy

<sup>2</sup> Dipartimento di Fisica e Scienze della Terra, Università degli Studi di Ferrara, Via Saragat 1, Ferrara, 44121, Italy

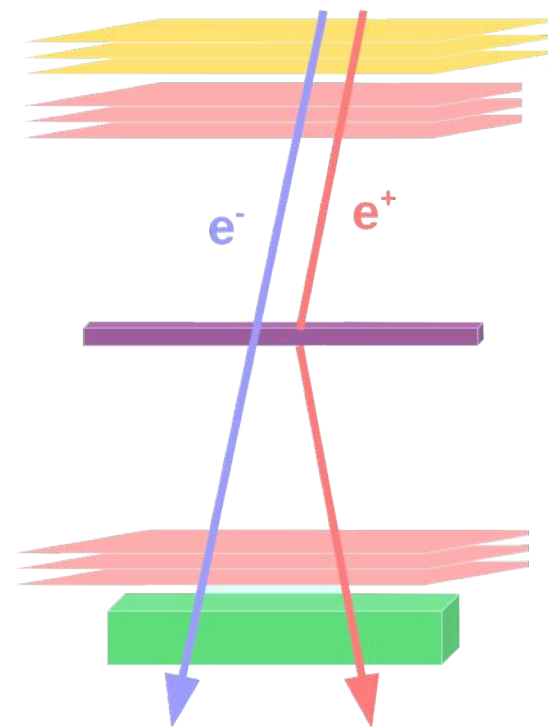
<sup>3</sup> Imperial College London, London SW7 2AZ, U.K.



# Is it possible to measure the $e^+/e^-$ ratio with a 1 cm bent crystal?



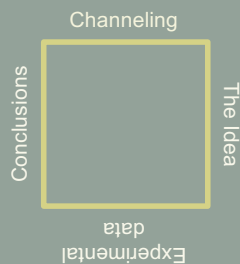
1 m

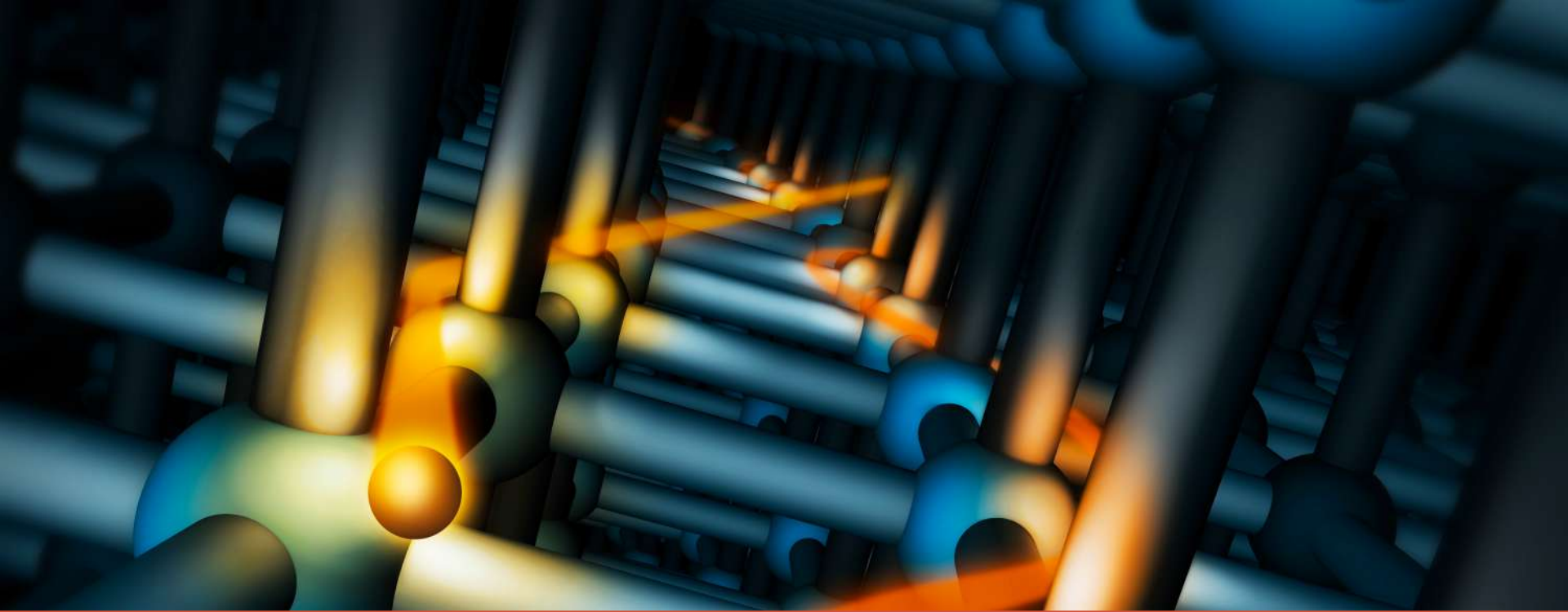


0.01 m

# Outline

- Channeling:
  - Channeling
  - De-channeling
  - Channeling in bent crystals
- The idea
  - Basic scheme
  - Positron to electron ratio measurement
- Experimental Data
  - CERN SPS-H4 line
- Conclusions
  - Spin precession & Enhanced bremsstrahlung
  - Conclusions

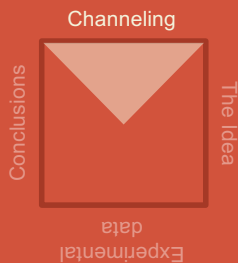




# CHANNELING

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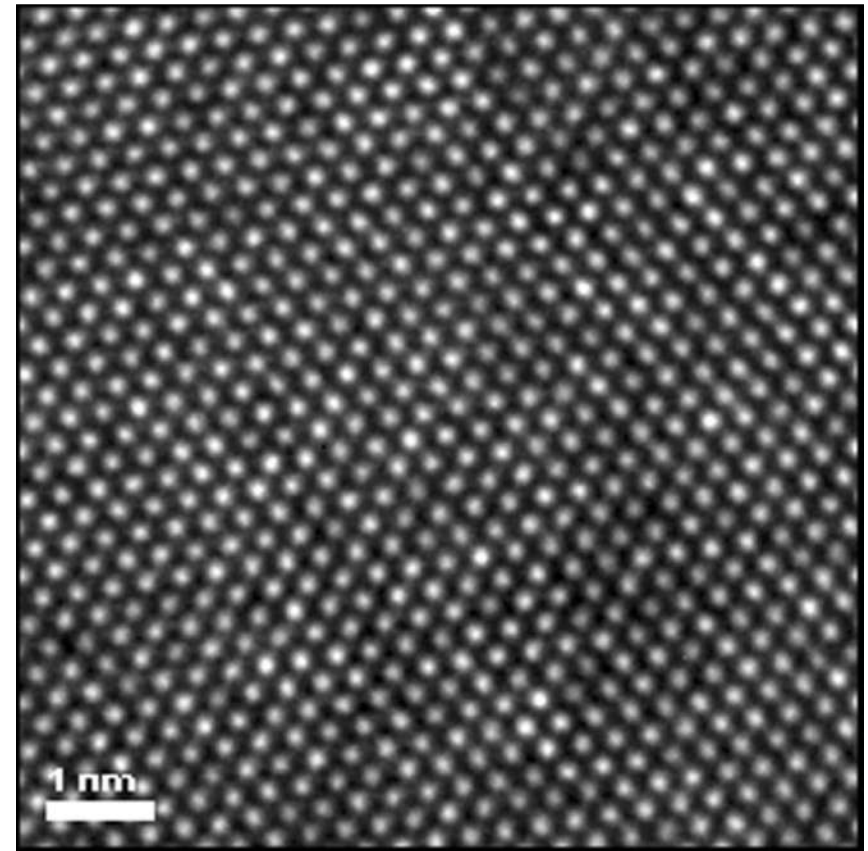
Entrapment of charged particles by the ordered pattern of crystalline atoms



# Channeling

- A crystal is a microscopically ordered pattern of atoms.

HRTEM image of a silicon (Si) [110] crystallographic zone axis.

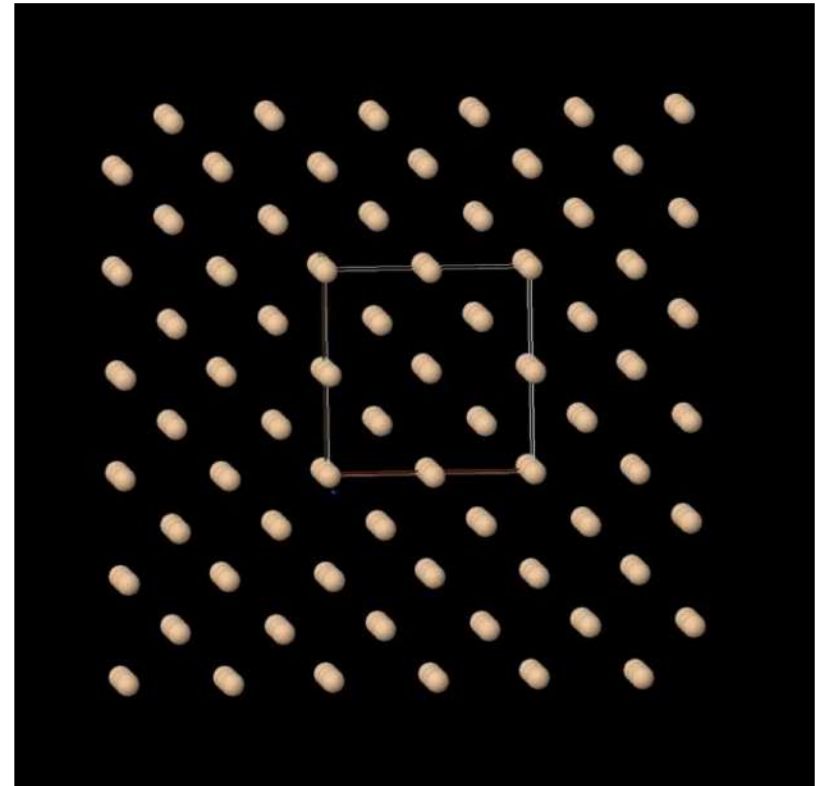


Ki-Bum Kim, SPIE Newsroom, DOI: 10.1117/2.1200812.1396

# Channeling

- A crystal is a microscopically ordered pattern of atoms.
- The periodic arrangement of atoms generates a series of crystal planes.

## Rotating Si crystal structure

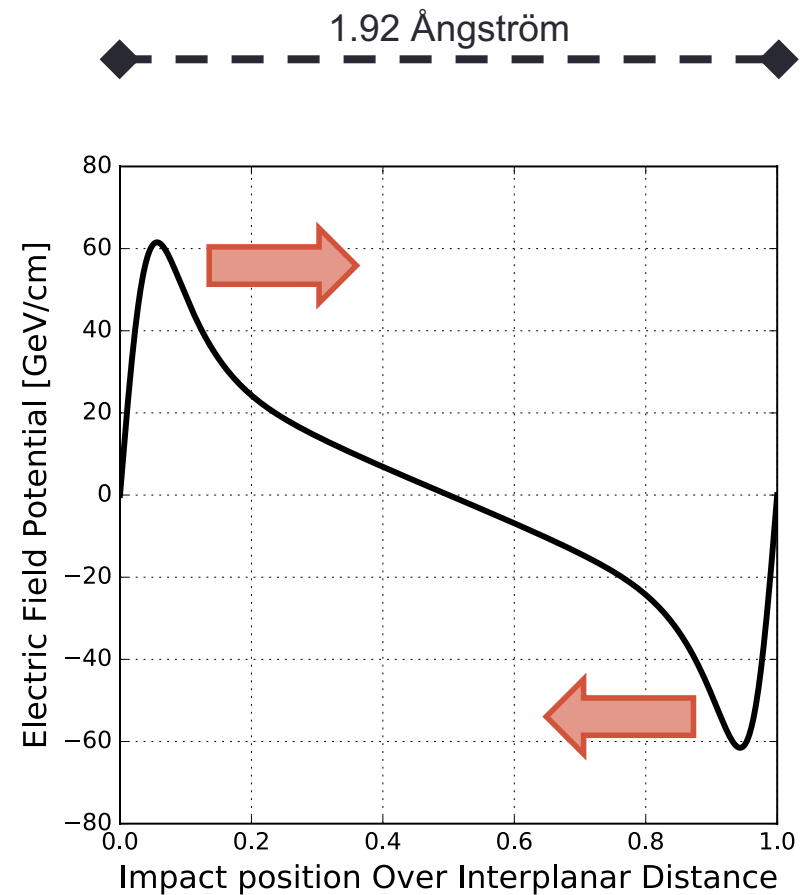


Jmol: an open-source Java viewer for chemical structures in 3D. <http://www.jmol.org/>

# Channeling

- A crystal is a microscopically ordered pattern of atoms.
- The periodic arrangement of atoms generates a series of crystal planes.
- The ordered charges of the planes generates a strong electromagnetic field.

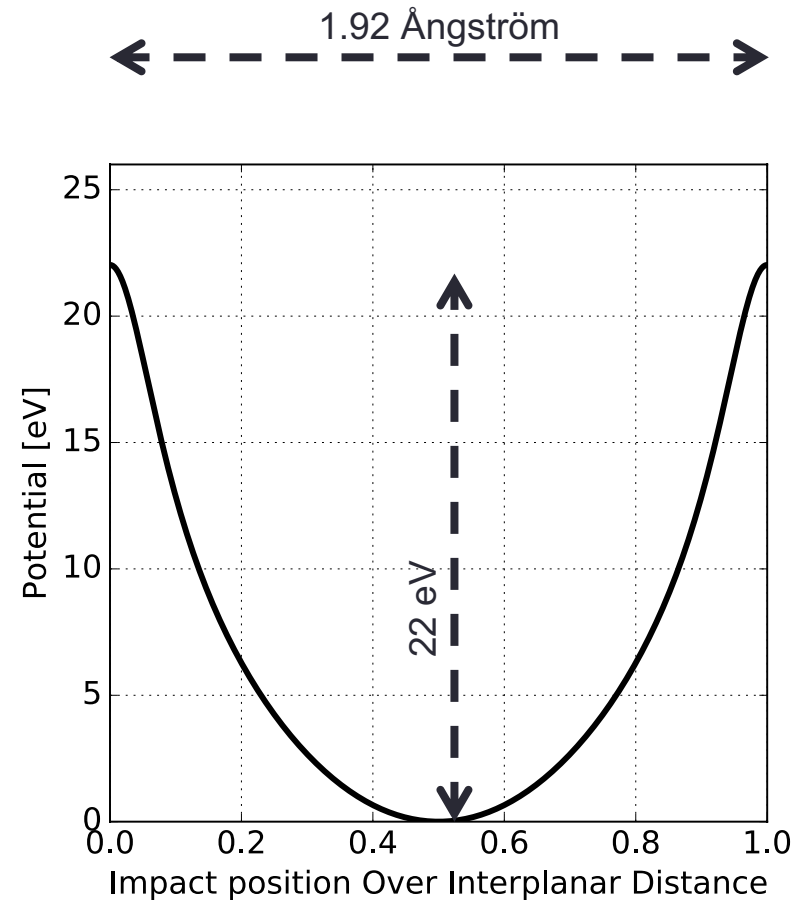
## Inter-planar electric field for Si (110)



# Channeling

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- The e.m. field generates a potential well able to constrain charged particles.

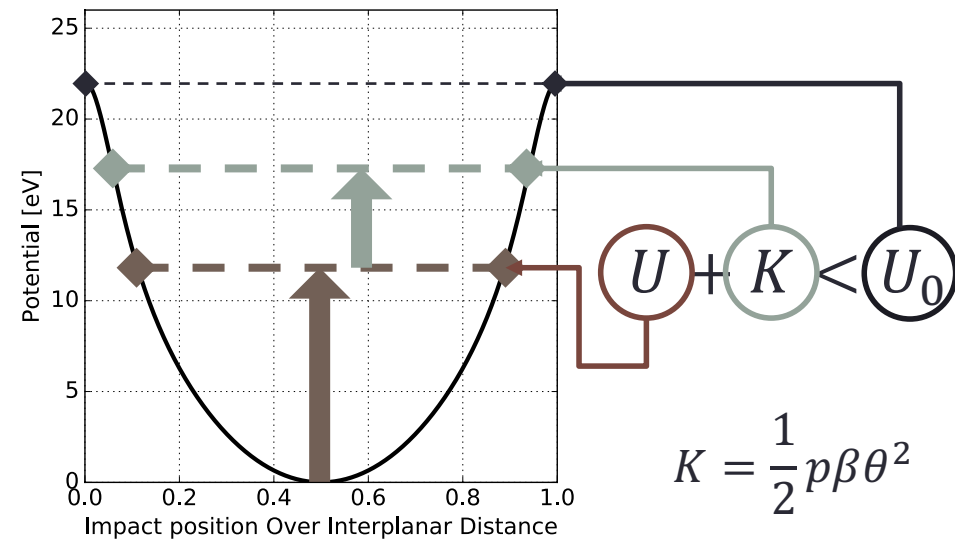
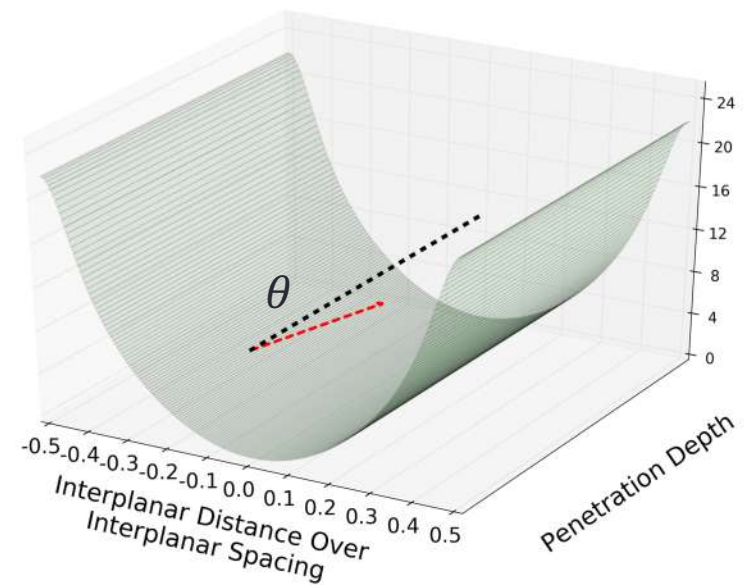
## Inter-planar potential for Si (110)





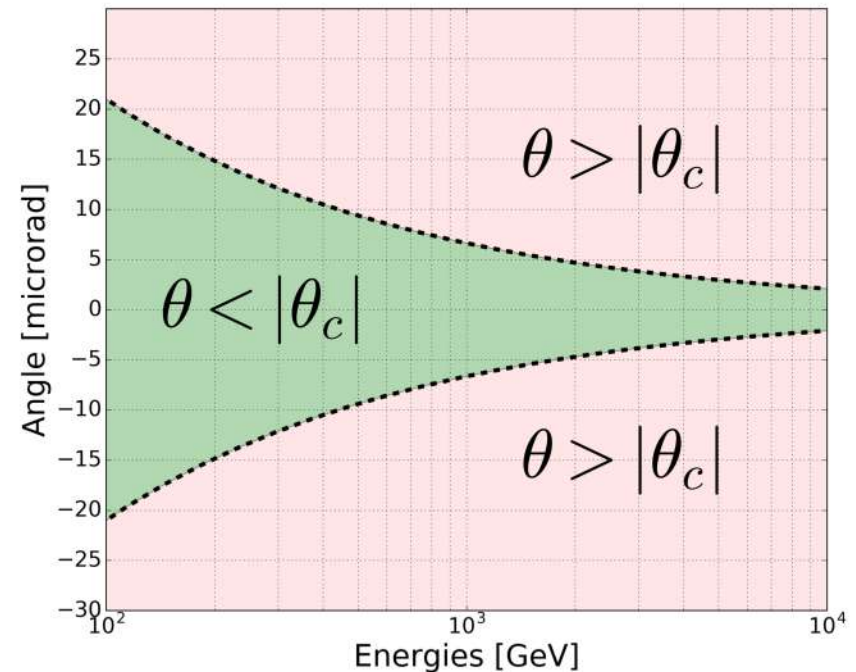
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- Channeling occurs when the angle between the particle trajectory and the crystallographic plane is lower than the channeling critical angle, i.e. when the potential energy is lower than the potential well barrier.
- The channeling critical angle is proportional to the square root of the well depth of the inter-planar potential divided by the particle energy. Therefore, channeling is a directional process, especially for high-energy particles.

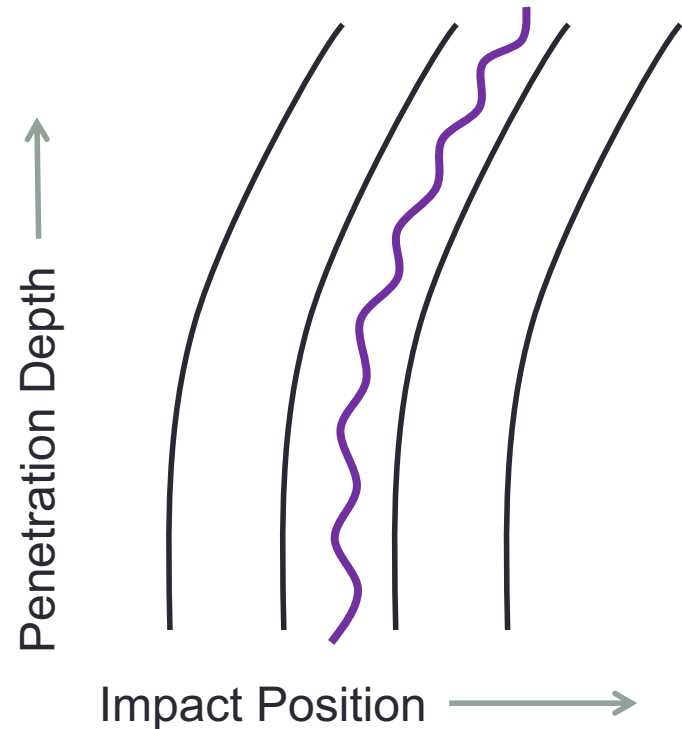


$$|\theta| < \theta_c = \sqrt{\frac{2U_0}{p\beta}}$$

# Channeling in bent crystals

- In 1976 E. N. Tsyganov asks himself an interesting question.

***“What will happen with the trajectory of the channeled particles if we bend the crystal? Up to some critical value of the bending radius a particle trajectory will repeat the shape of a bent crystal.”***

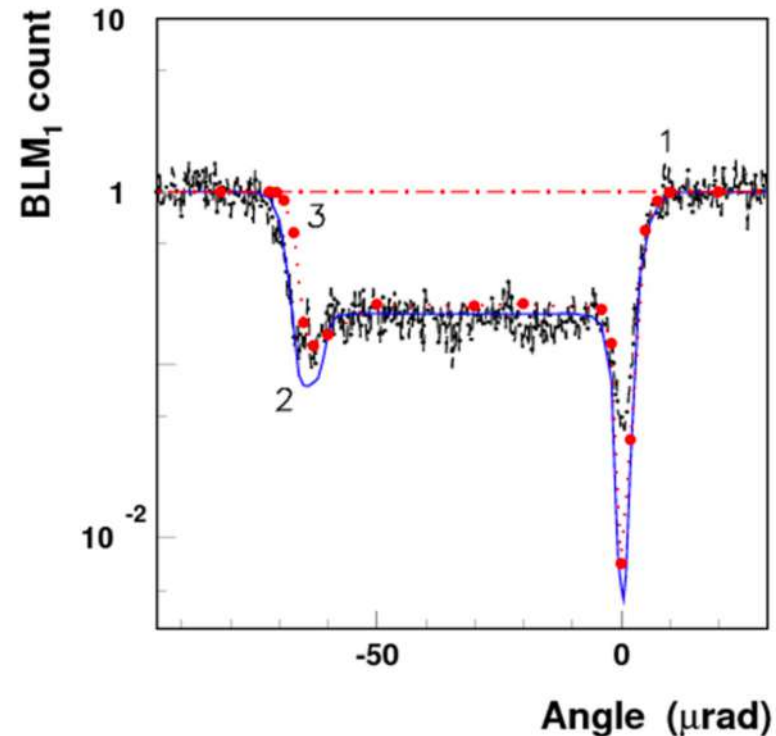


E. Tsyganov, “Some aspects of the mechanism of a charge particle penetration through a monocystal.” Tech. rep., Fermilab (1976) Preprint TM-682

# Channeling in bent crystals

- In 1976 E. N. Tsyganov asks himself an interesting question.
- Channeling in bent crystals was observed from 855 MeV/c  $e^-$  (MAMI) to 6.5 TeV/c proton (LHC).

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W. Scandale et al., “Observation of channeling for 6500 GeV/c protons in the crystal assisted collimation setup for LHC” Physics Letters B 758 (2016), 129

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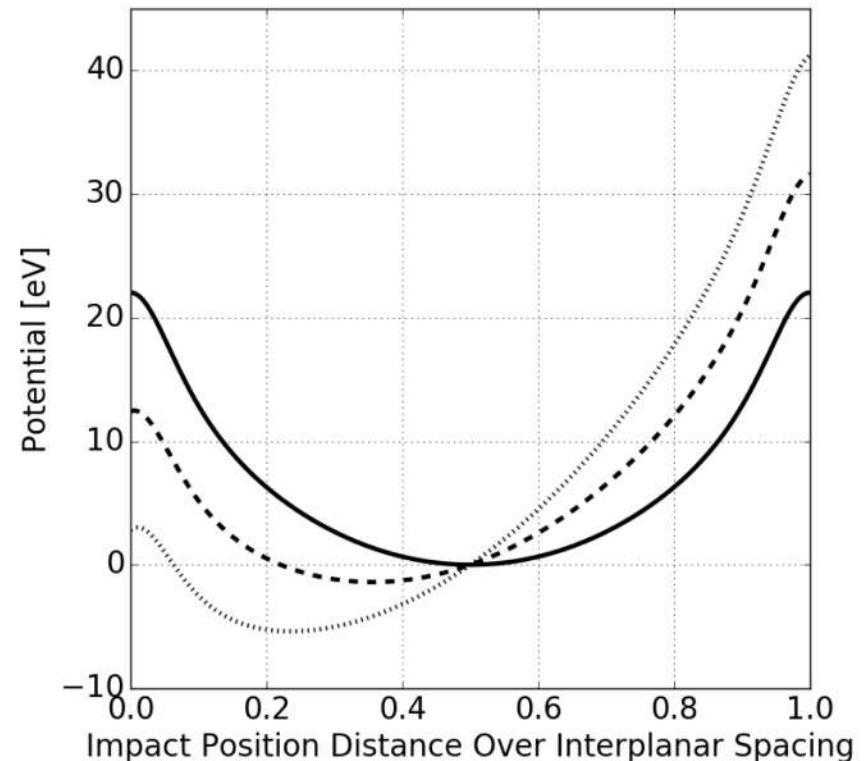
# Channeling in bent crystals

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- Channeling in bent crystals was observed from 195 MeV/c  $e^-$  (MAMI) to 6.5 TeV/c proton (LHC).
- Curvature affects particle motion causing a centrifugal force, lowering the potential well barrier.

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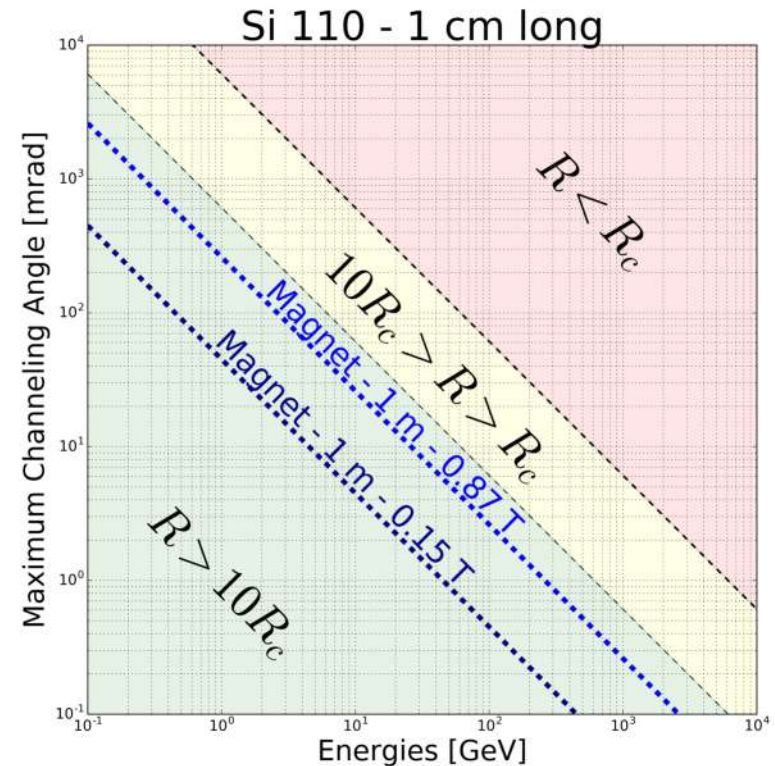
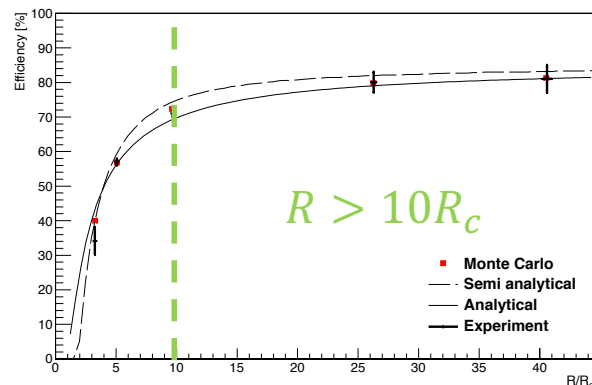
Inter-planar potential for Si (110)



$$p\beta \frac{d^2x}{dz^2} U'(x) + \frac{p\beta}{R(z)} = 0$$

# Channeling in bent crystals

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- Channeling in bent crystals was observed from 195 MeV/c  $e^-$  (MAMI) to 6.5 TeV/c proton (LHC).
- Curvature affects particle motion causing a centrifugal force, lowering the potential well barrier.
- The maximum achievable bending angle is determined by the critical radius, proportional to the particle momentum-velocity. At  $10R_c$  the efficiency is almost the maximum achievable.



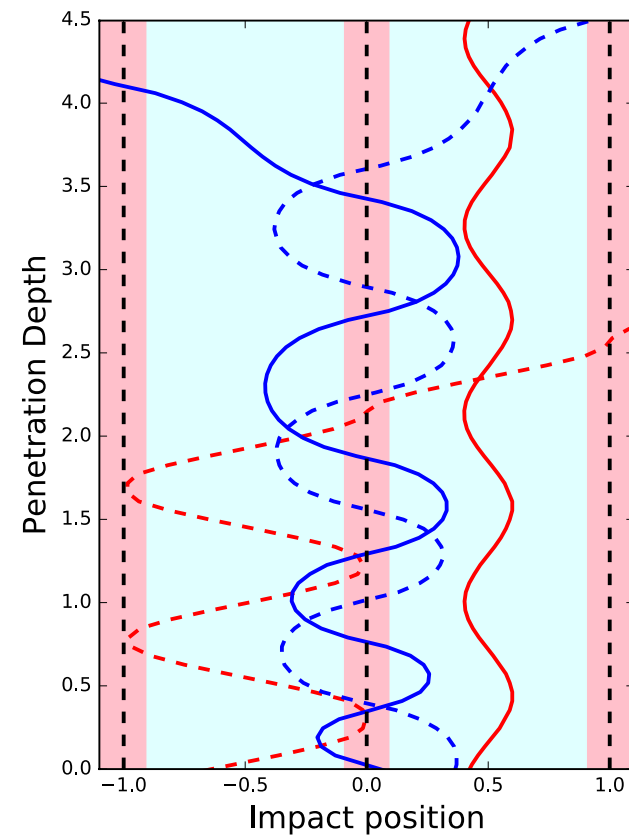
$$R_c = \frac{p\beta}{U'_{max}}$$



# Dechanneling

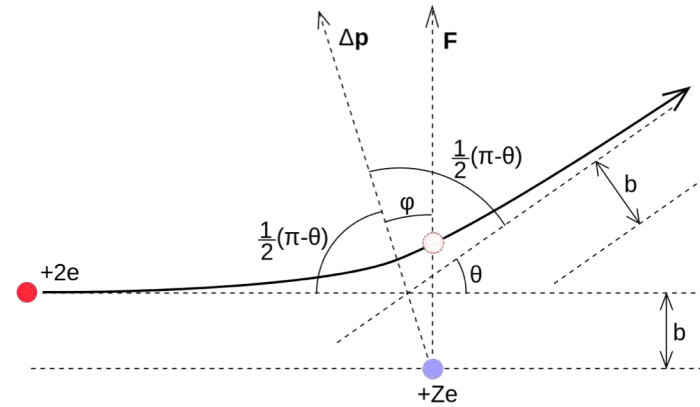
- A particle that leaves the channeling state undergoes the “*dechanneling*” process.

Positrons and Electrons trajectories under channeling in a Si (110)

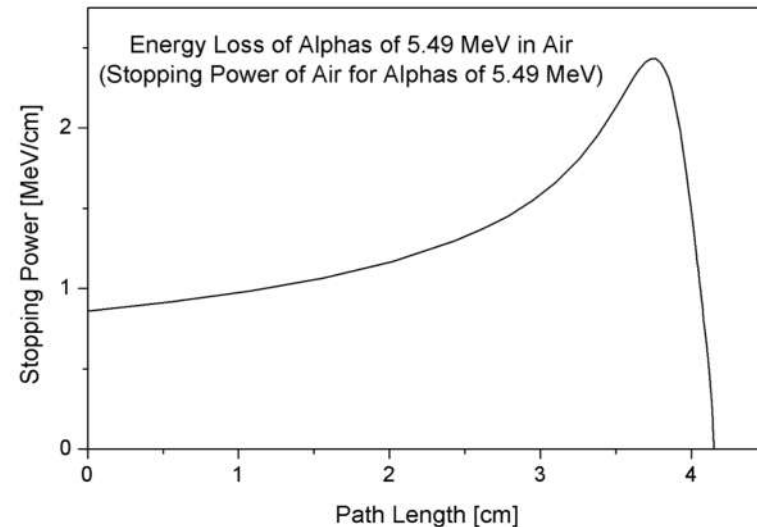


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- A particle that leaves the channeling state undergoes the “*dechanneling*” process.
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Wikimedia Commons, the free media repository

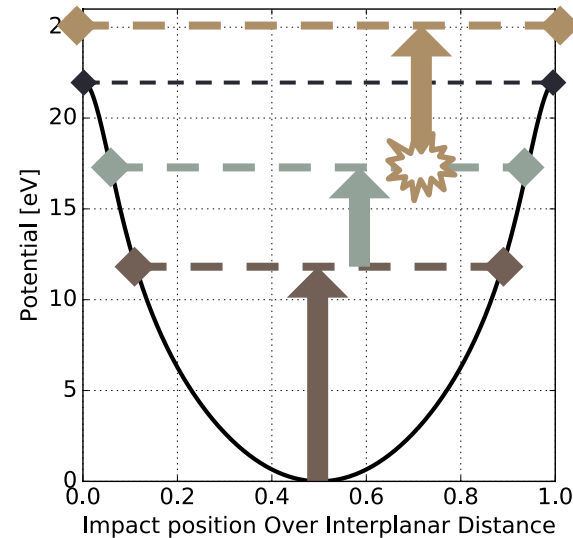
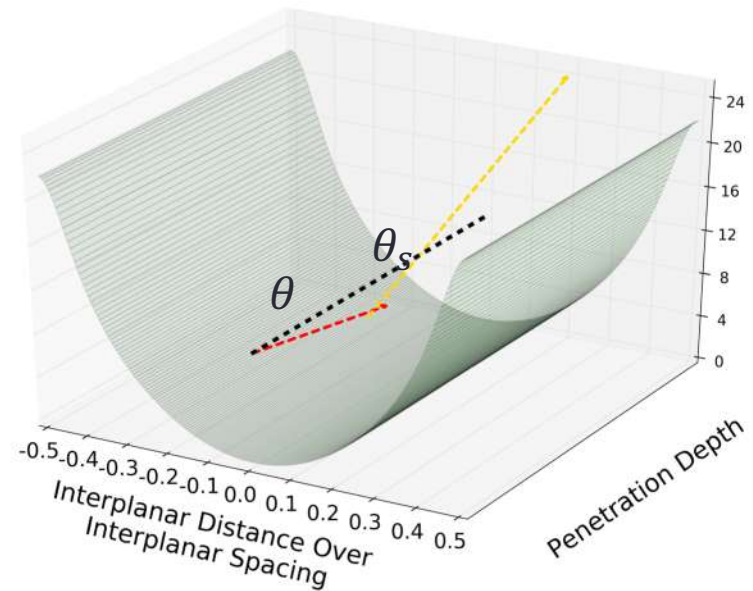


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- Incoherent interactions increase the particle transverse energy until it exceeds the potential well barrier.

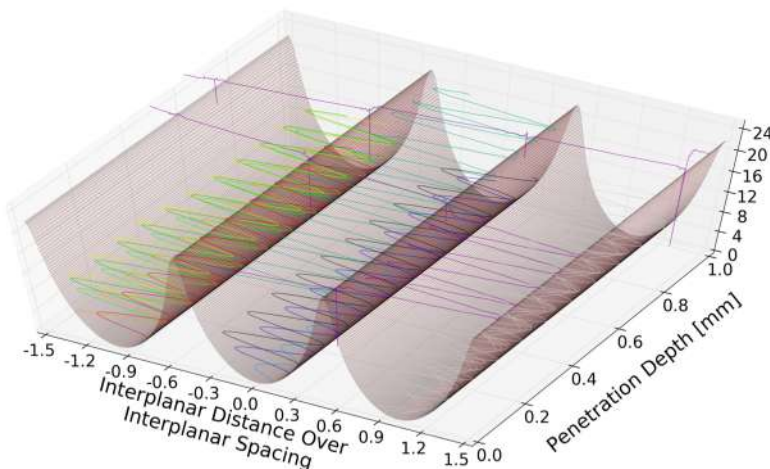
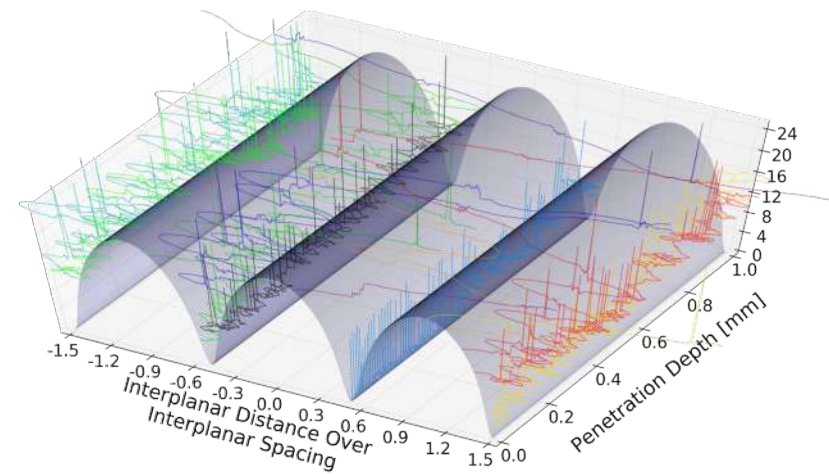
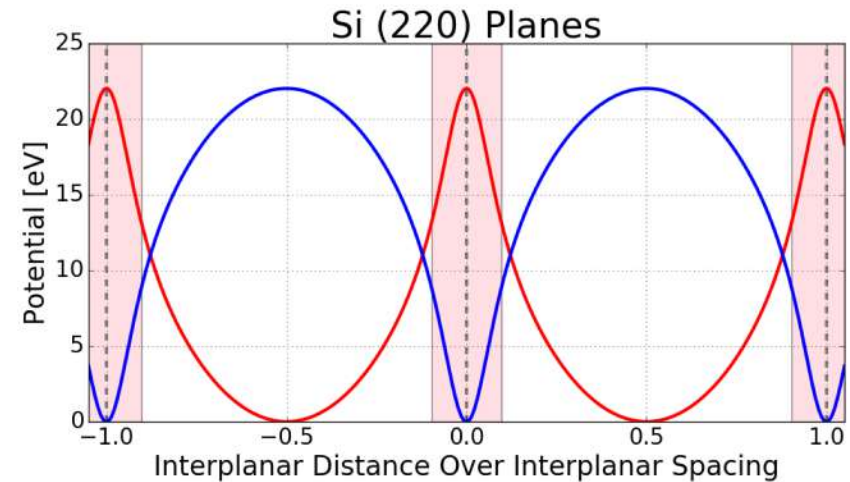


$$U + K < U_0$$

$$K = \frac{1}{2} p \beta \theta^2 + \Delta K$$

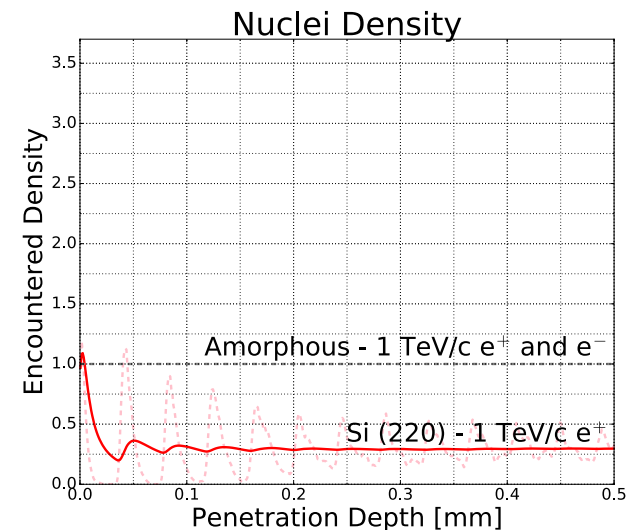
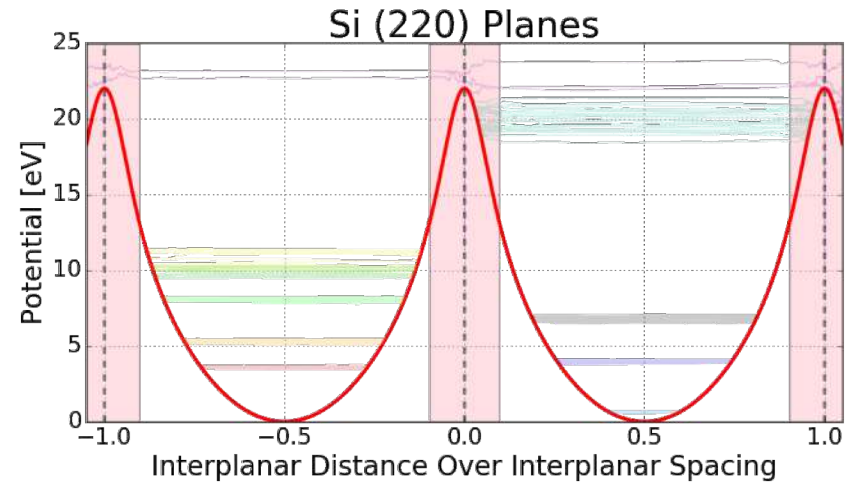
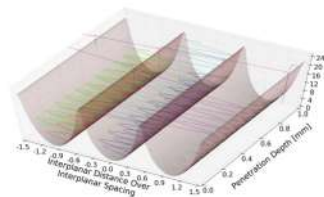
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- Channeling depends on particle charge sign:



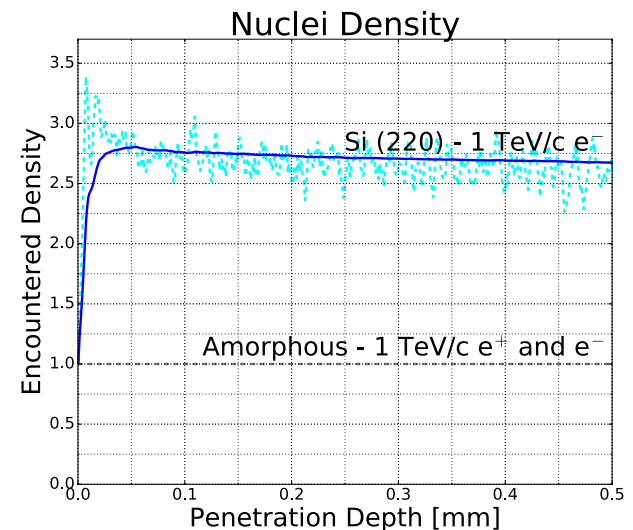
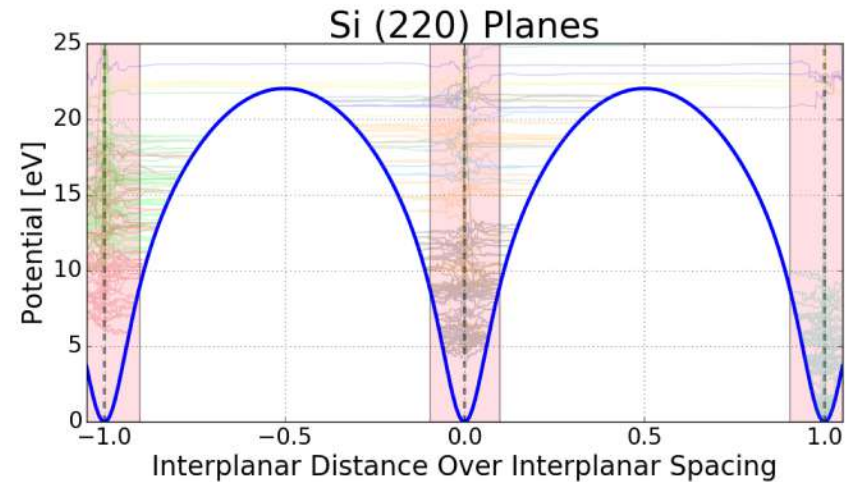
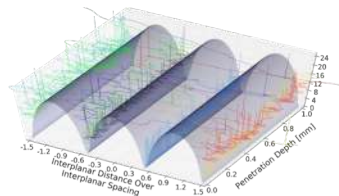
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  - A positively charged particle that oscillates **between** two planes **rarely** interacts with the atomic nuclei.



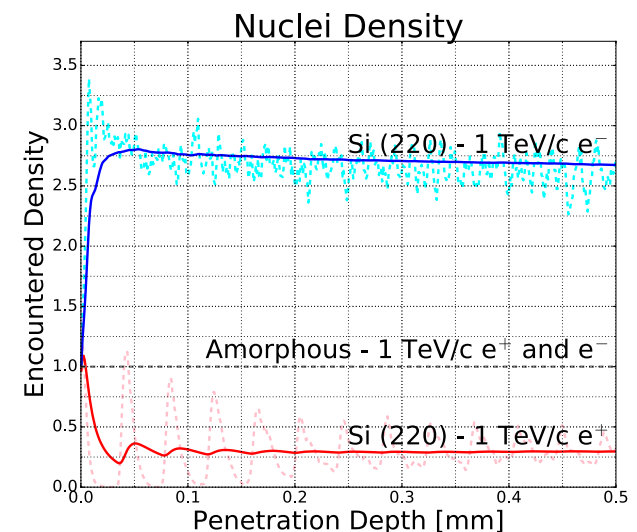
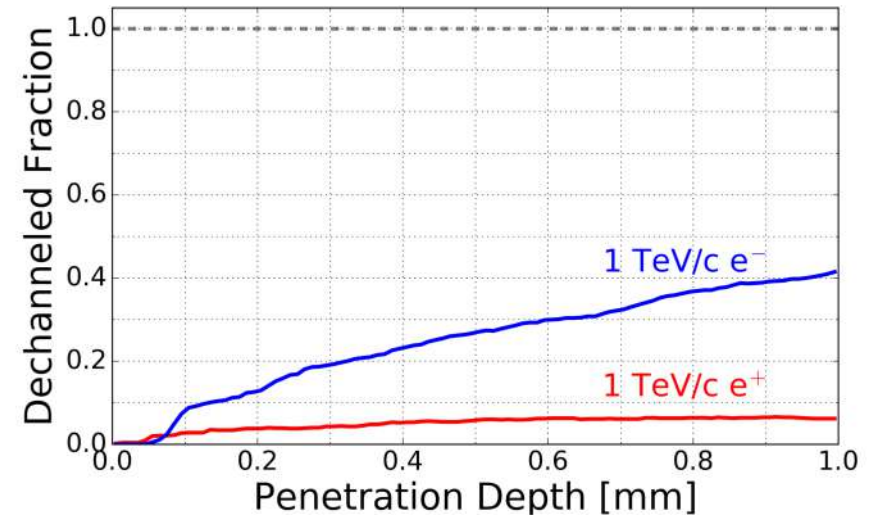
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# Dechanneling

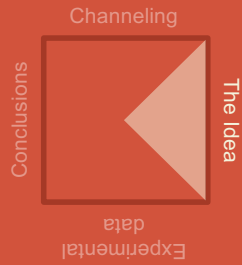
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- ***Electrons dechannel more frequently than Positrons***





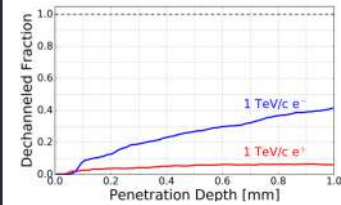
# THE IDEA

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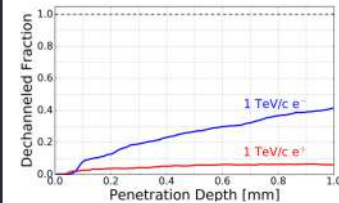
# Basic scheme

Different dechanneling rate  
for positive and negative  
particles

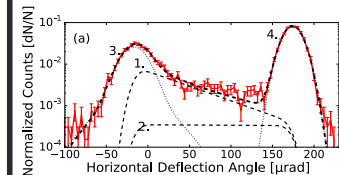


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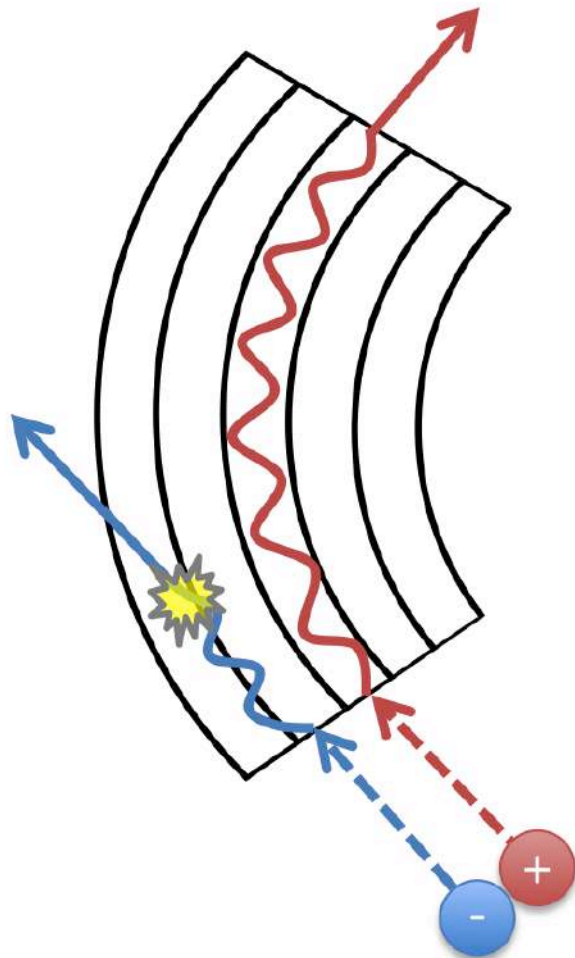


Deflection of charged  
particles under channeling  
in bent crystals

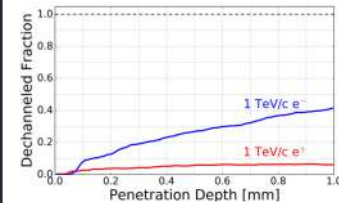




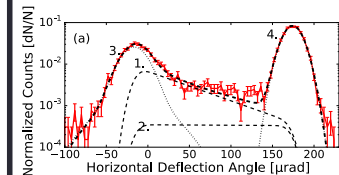
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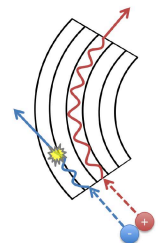
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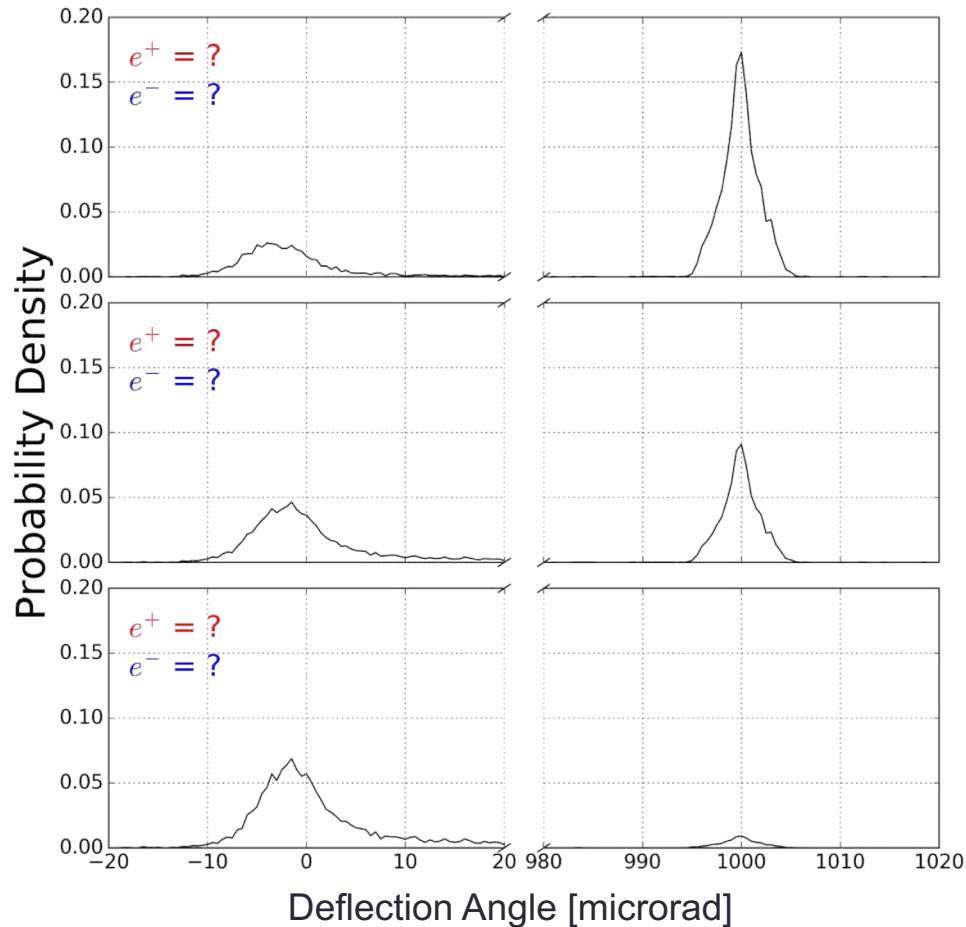


Positron to electron ratio  
measurement via channeling



# Positron to electron ratio measurement

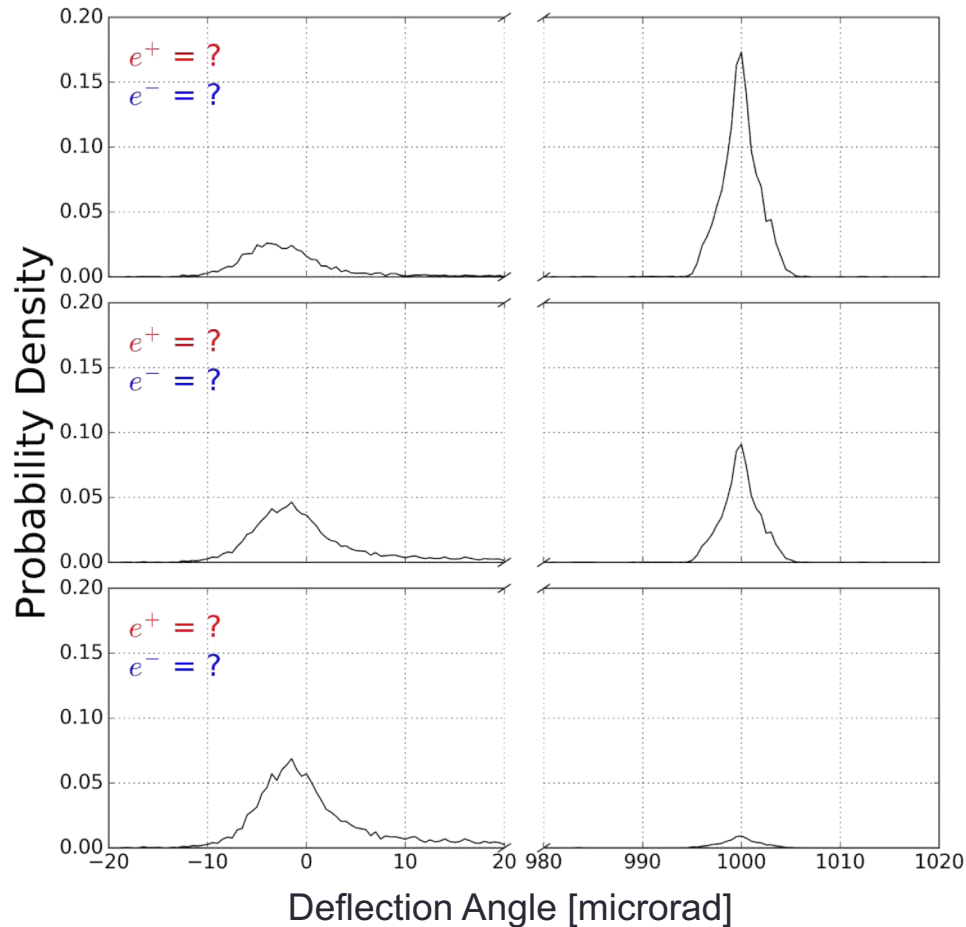
$e^+/e^-$  1 TeV/c beam  
Si (220) Crystal – 1 cm long and 1 mrad bending



- By analysing a beam deflection distribution after the interaction with a bent crystal it is possible to determine the ratio between positrons and electrons.

# Positron to electron ratio measurement

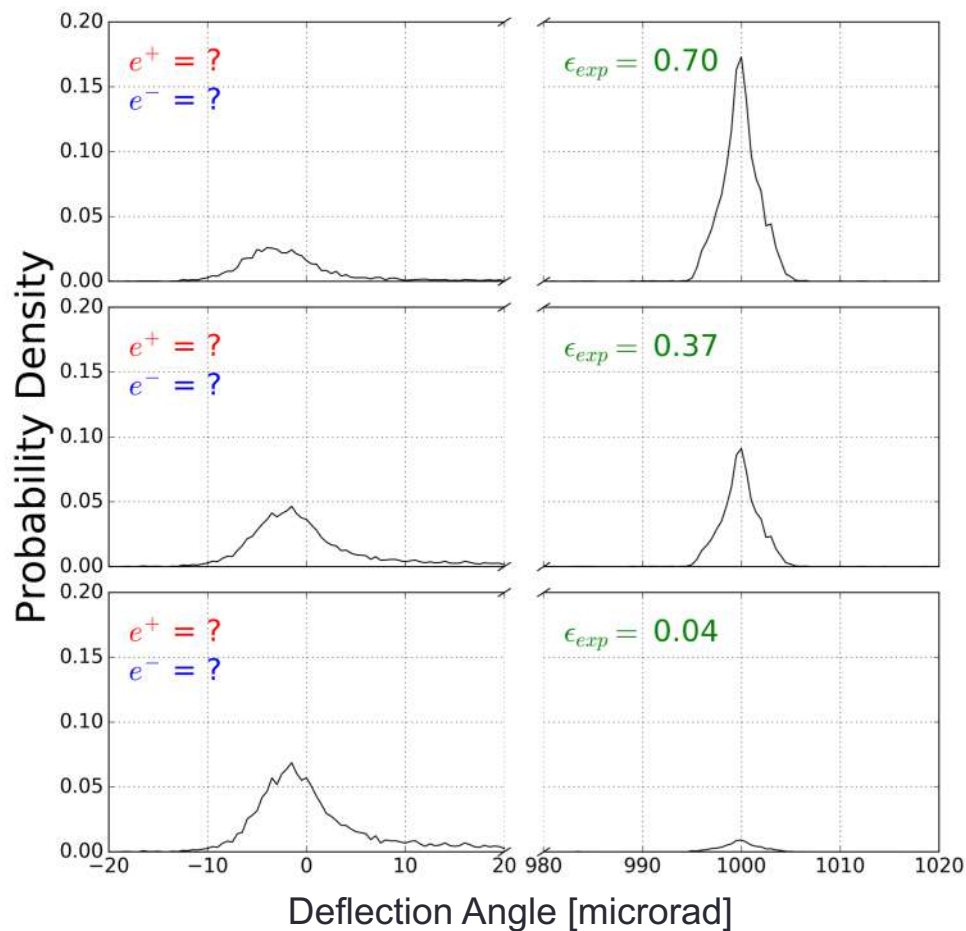
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# Positron to electron ratio measurement

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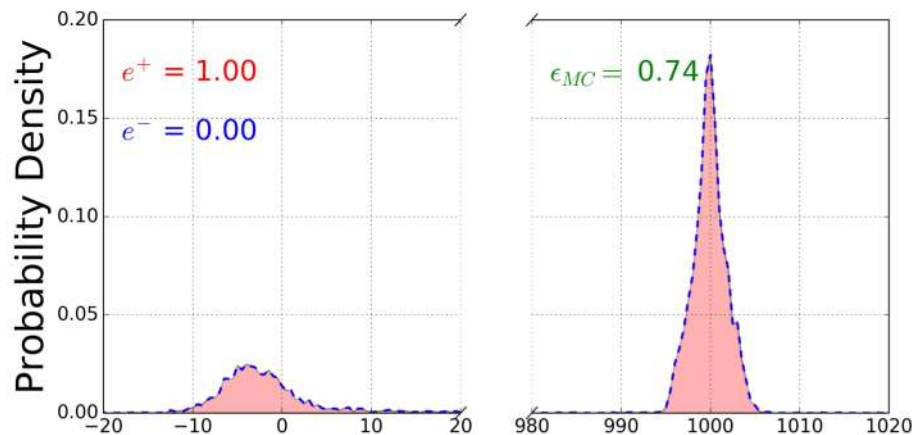
- By analysing a beam deflection distribution after the interaction with a bent crystal it is possible to determine the ratio between positrons and electrons.
- Two ingredients are needed:
  - Experimental deflection distribution

# Positron to electron ratio measurement

$e^+/e^-$  1 TeV/c beam

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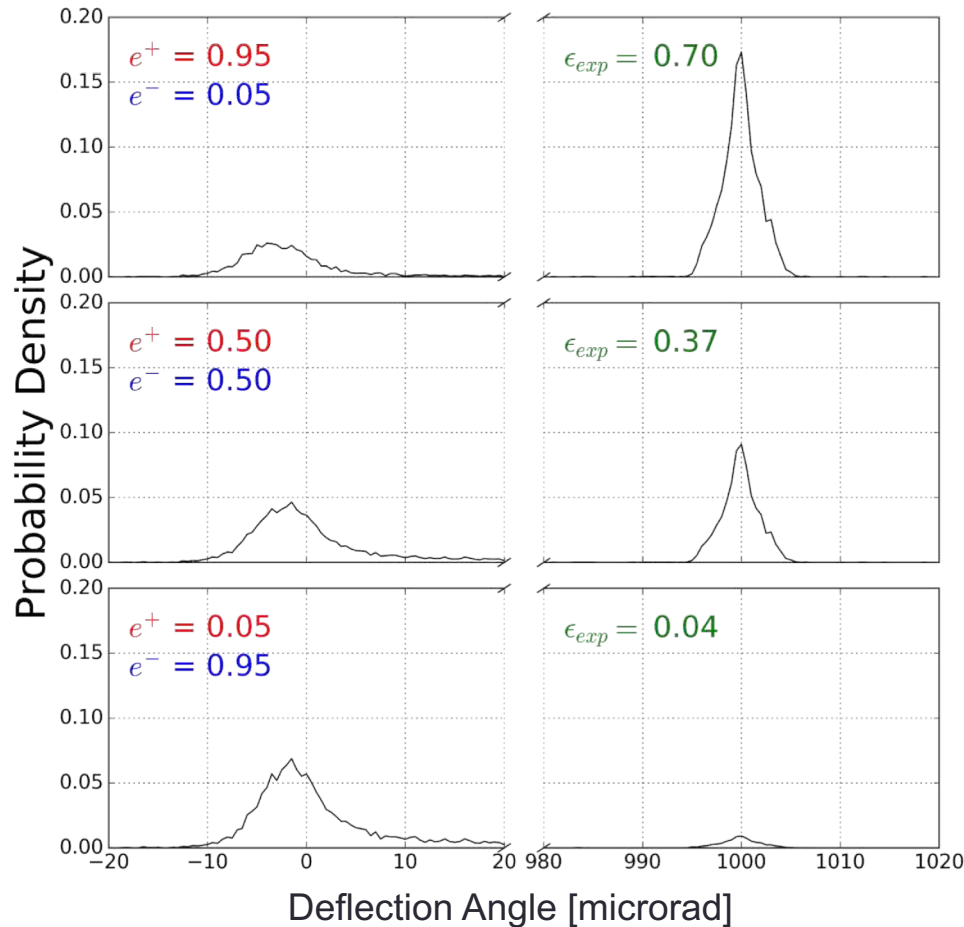


- Two ingredients are needed:
  - Experimental deflection distribution
  - Monte Carlo

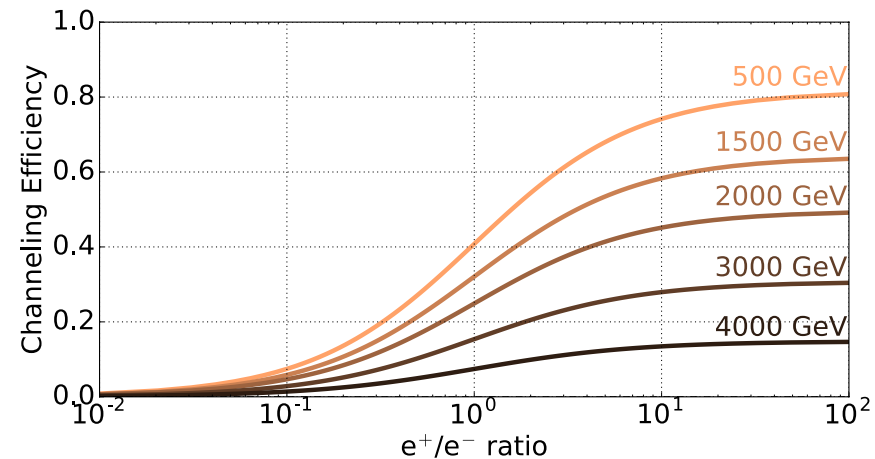
Deflection Angle [microrad]

# Positron to electron ratio measurement

$e^+/e^-$  1 TeV/c beam  
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- By analysing a beam deflection distribution after the interaction with a bent crystal it is possible to determine the ratio between positrons and electrons.
- Two ingredients are needed:
  - Experimental deflection distribution
  - Monte Carlo
- As a result, it is possible to determine the ratio of positrons over electrons with channeling.



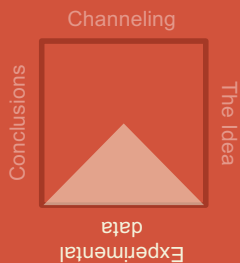
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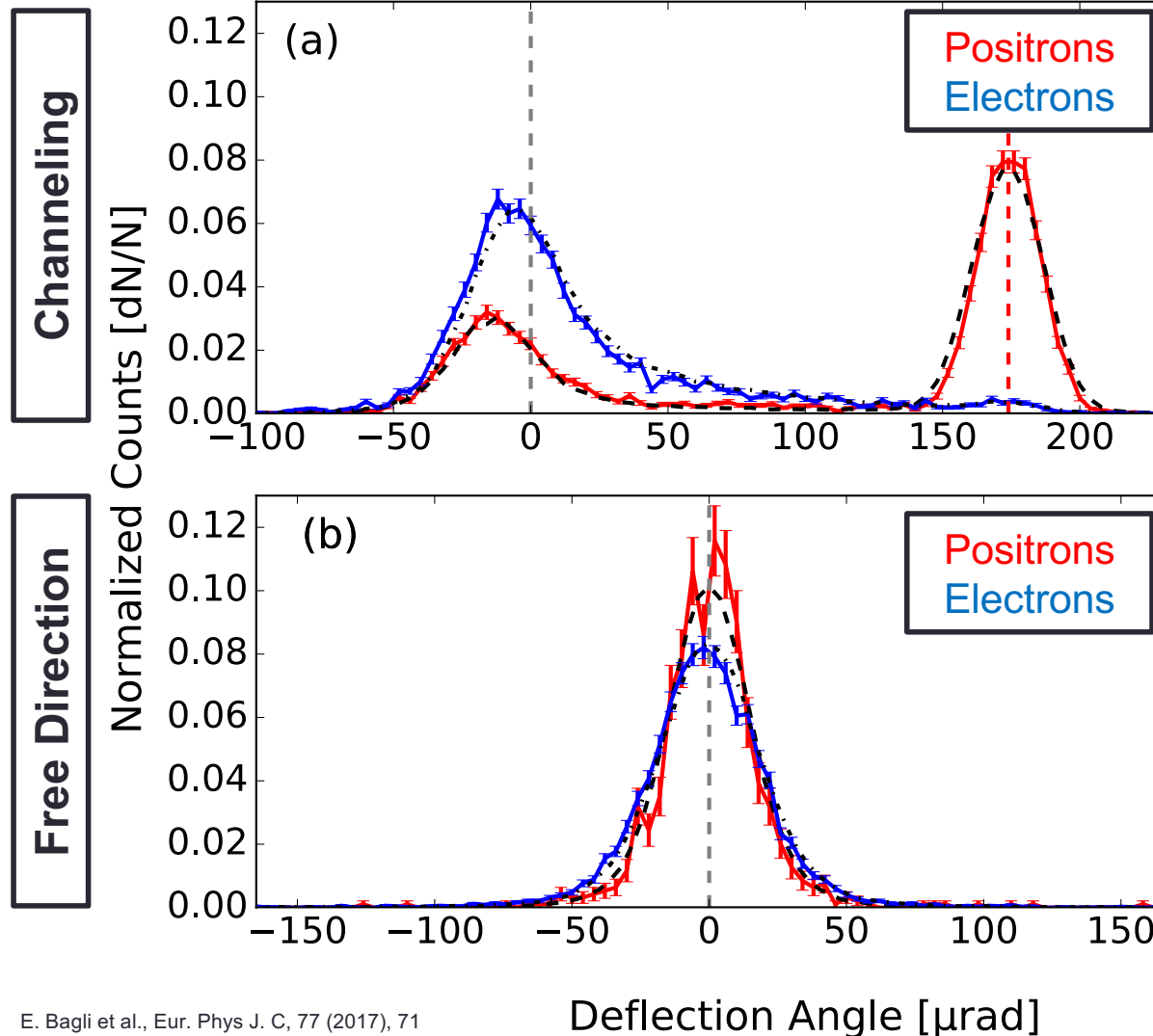
# EXPERIMENTAL DATA

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Test beam at the CERN SPS-H4 line

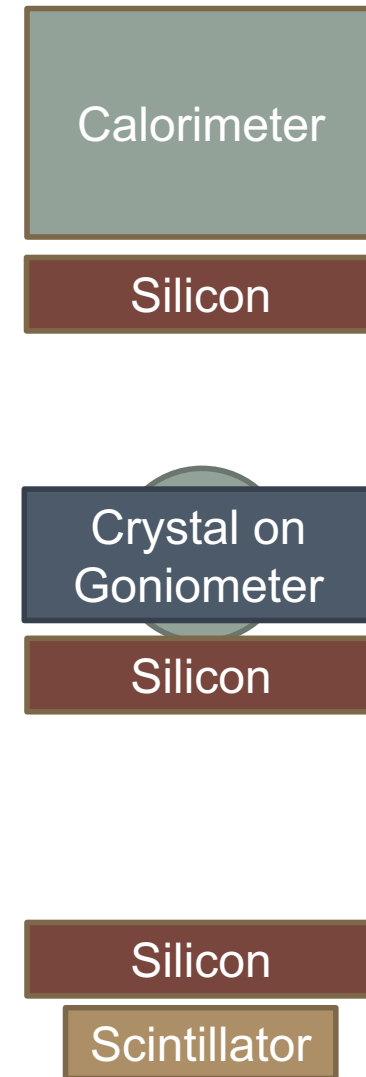
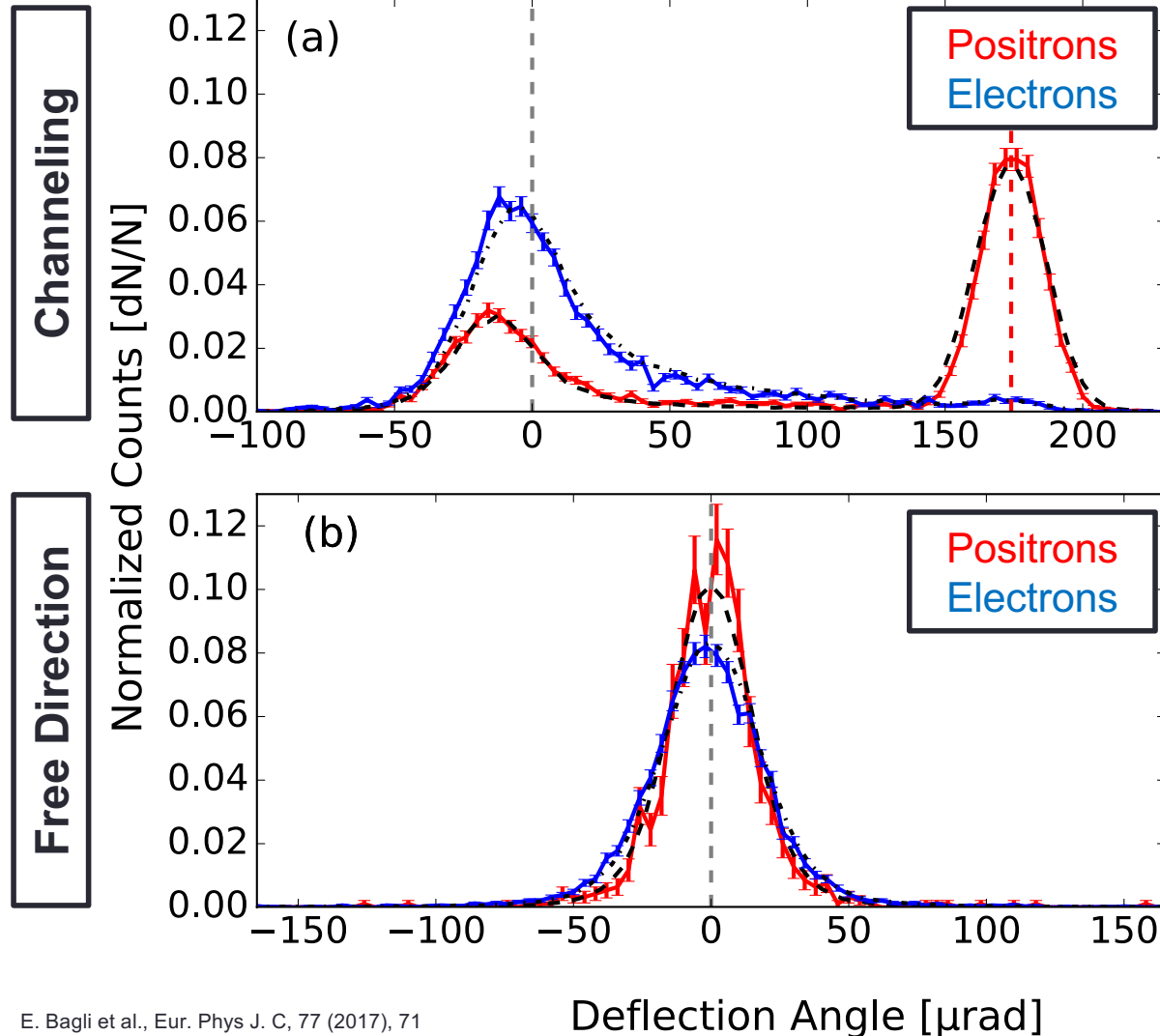


# CERN SPS-H4 line

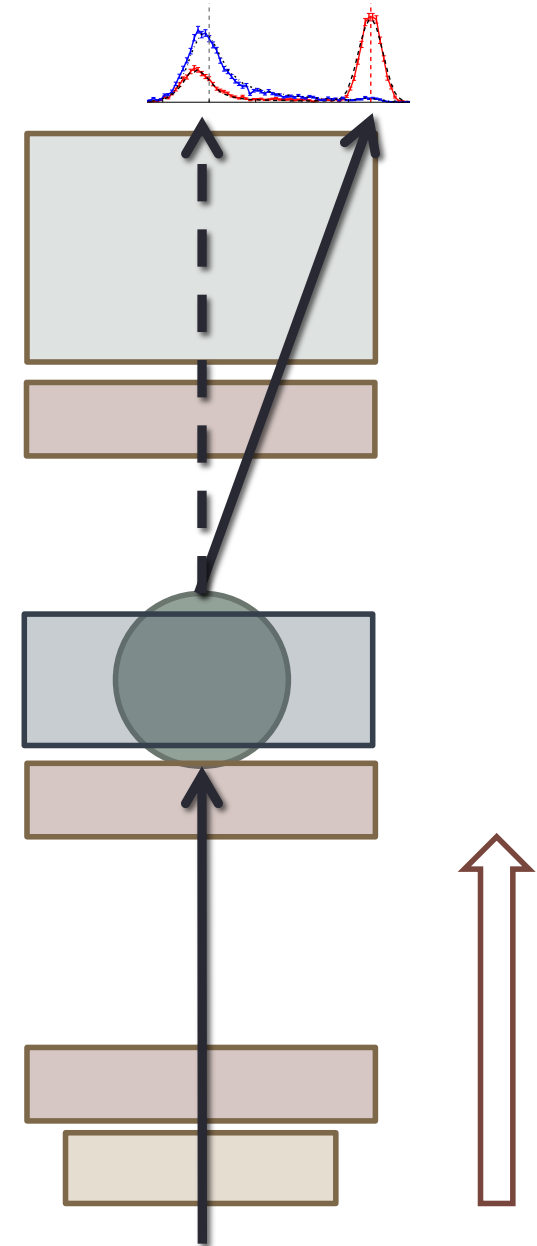
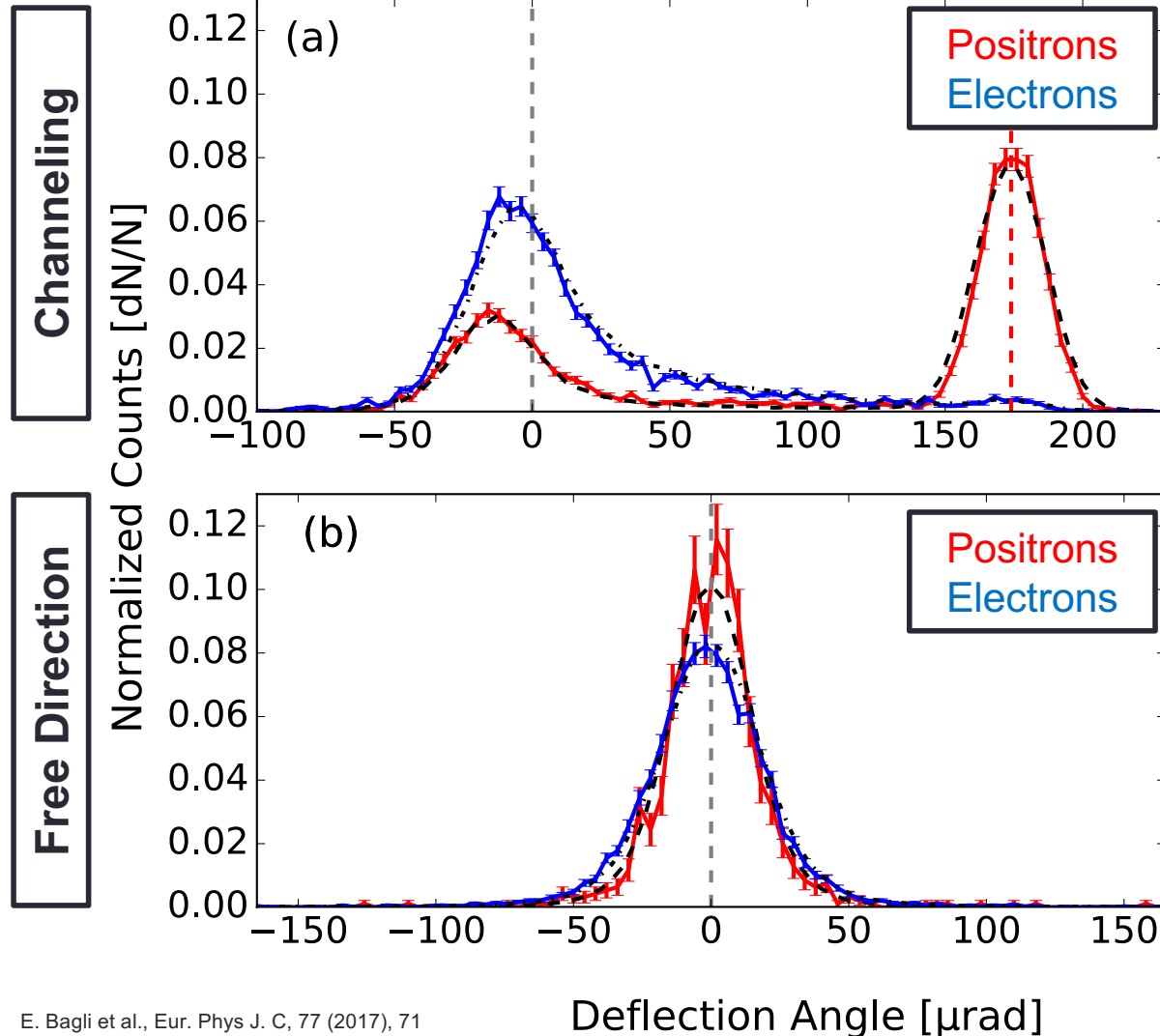




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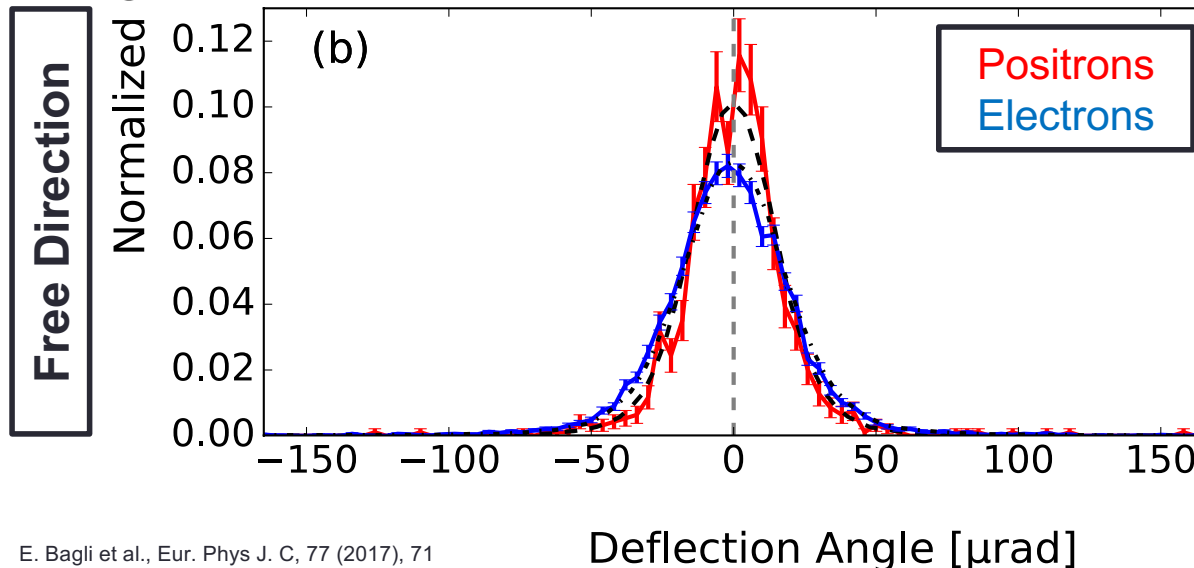
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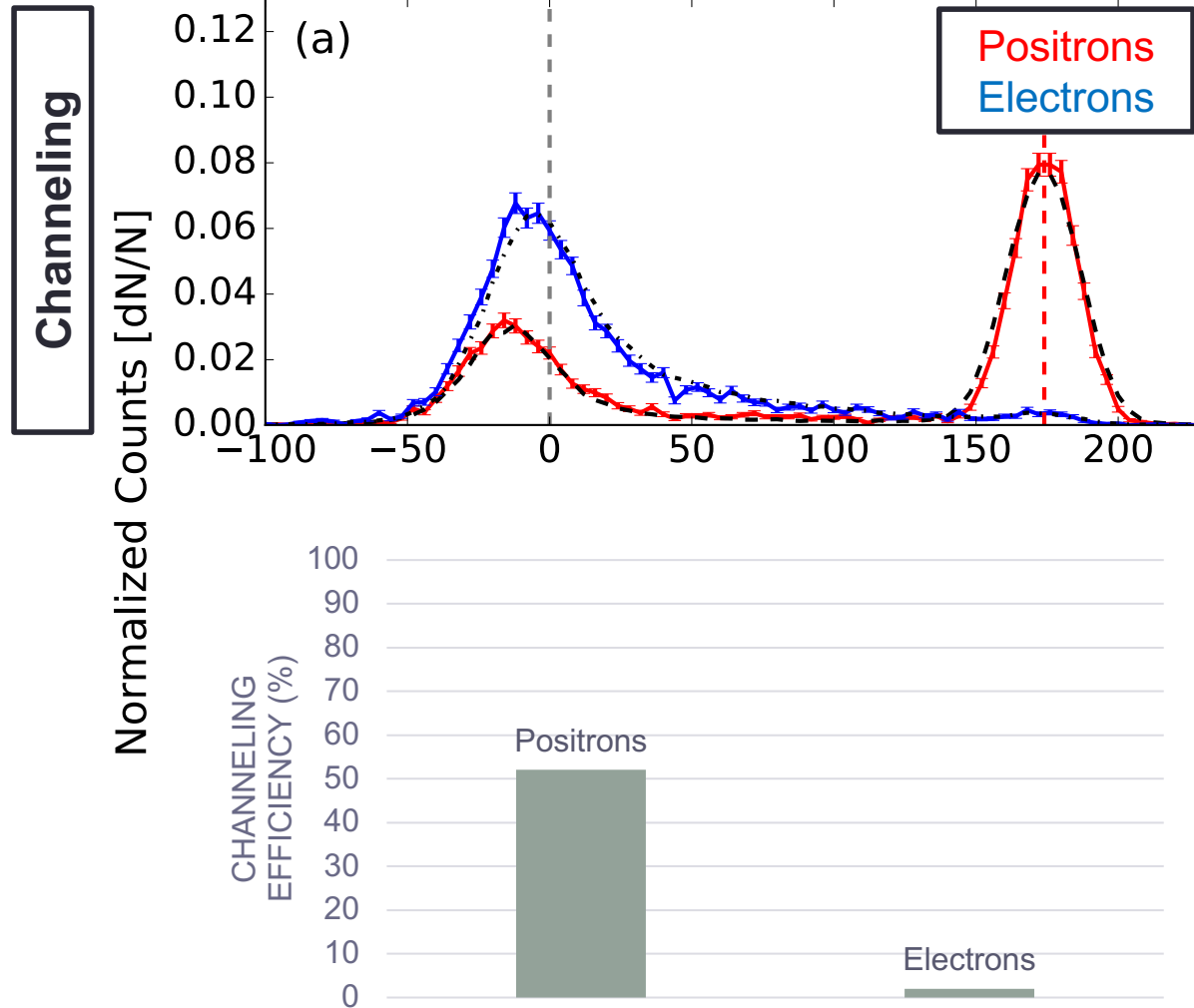


Particle	Condition	r.m.s. (μrad)
e <sup>+</sup> /e <sup>-</sup>	Not Aligned	8.8 ± 0.1
e <sup>+</sup>	Channeling	7.6 ± 0.4
e <sup>-</sup>	Channeling	10.3 ± 0.2



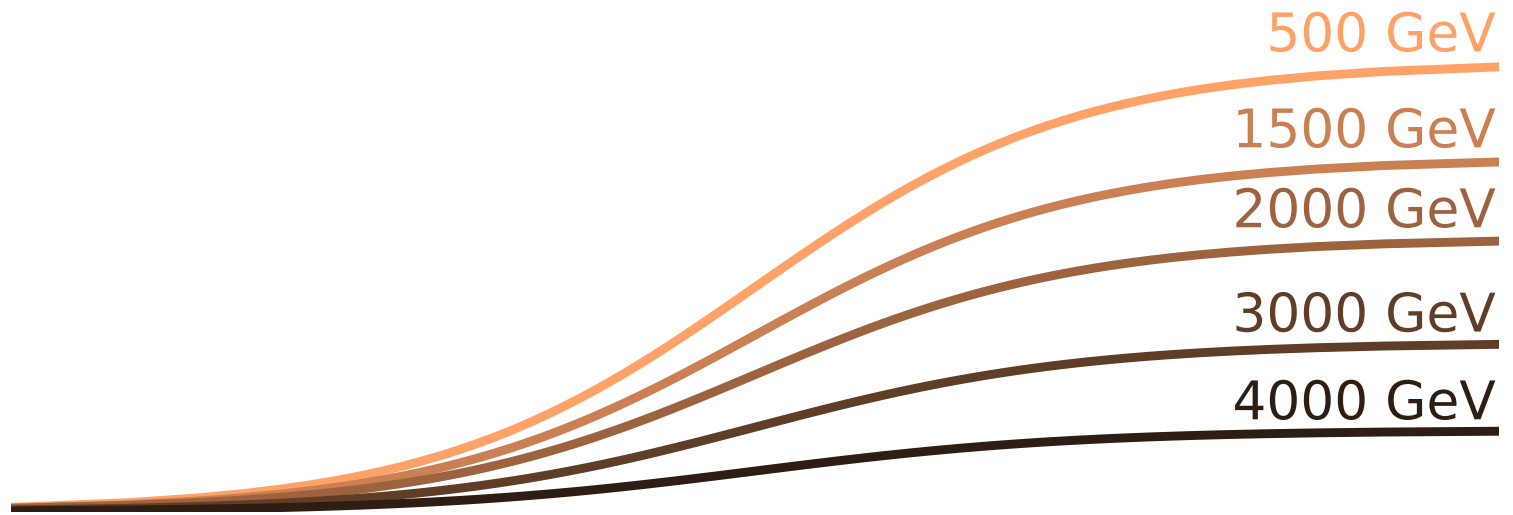
Electrons interact more frequently than positrons with nuclei, leading to an increase in the r.m.s. of the deflection distribution in the free direction.

# CERN SPS-H4 line



The channeling efficiency is by far greater for positrons rather than for electrons.

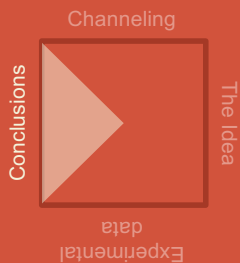
Particle	Channeling Efficiency (%)
$e^+$	$54 \pm 2$
$e^-$	$2 \pm 2$



# CONCLUSIONS

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And other usages of coherent effects



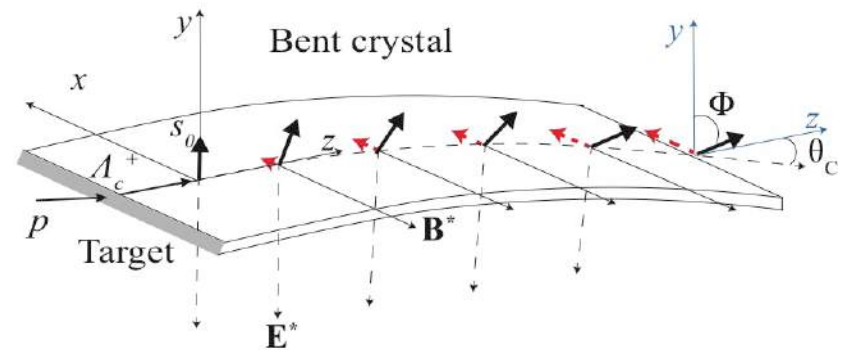
# Spin precession

- The spin precession of a charged particle is induced by the interaction of its electromagnetic dipole moments, e.g. MDM and EDM, with external electromagnetic fields.
- The intense electric field between the crystal planes,  $E$ , which deflects charged particles, transforms into a strong electromagnetic field  $E^* \approx \gamma E$ ,  $B^* \approx -\gamma \beta \times E/c$  in the instantaneous rest frame of the particle and induces spin precession. In the limit of large boost, the spin precession induced by the MDM is:

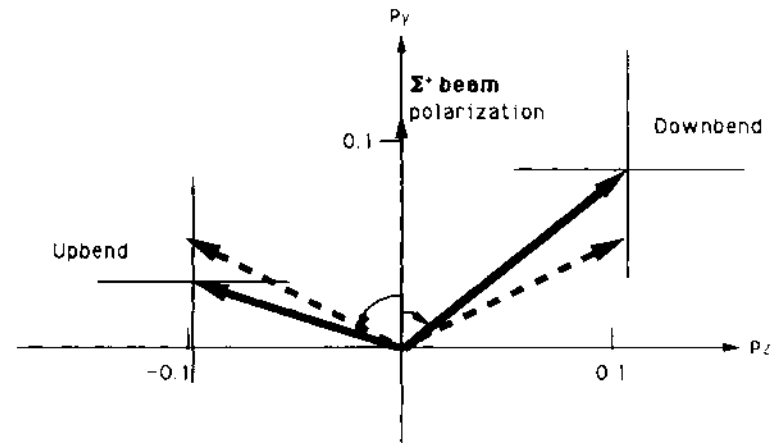
$$\phi = \frac{g-2}{2} \gamma \theta_c$$

- Thanks to the extremely large magnitude of the electric field, the spin rotation angle in the crystal of several centimetres in length can reach several radians.

- V. G. Baryshevsky, Pis'ma. Zh. Tekh. Fiz. 5 (1979), 182
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D. Chen et al., Phys. Rev. Letters 69 (1992), 3286



# Compact Calorimeters with Oriented Crystals



Presenter: **Laura Bandiera**, INFN Sezione di Ferrara - [bandiera@fe.infn.it](mailto:bandiera@fe.infn.it) -

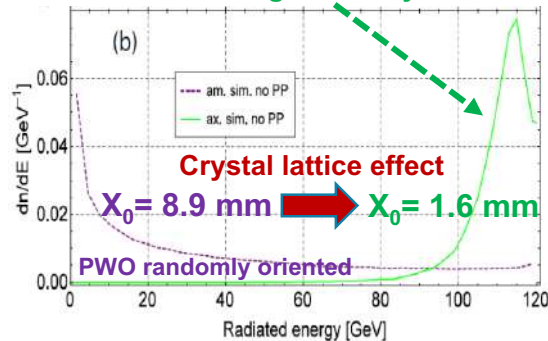
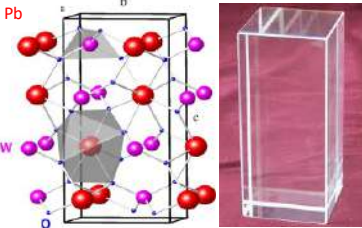


## Motivation

The radiation length in an oriented crystal is strongly reduced !!

PWO  $X_0$  reduction for electrons aligned to crystal axes

PbWO<sub>4</sub> scintillator crystal  
 $X_0$  standard = 8.9 mm



## Possible Application Potentialities

□ **FIXED-TARGET EXPERIMENT**: forward e.m. calorimeters/preshower with reduced volume.

□ **BEAM DUMP**: compact active beam dump with an increase of sensitivity to dark photons.

□ **SATELLITE TELESCOPE**: Containing e.m. showers for energies > 10 GeV in a smaller volume. **BORNE GAMMA-RAY**  
Cost reduction, increase of sensitivity and energy resolution!

*L. Bandiera et al, ArXiv: 1803.10005*

# Is it possible to measure the $e^+/e^-$ ratio with a 1 cm bent crystal?

1. Particles impinging on a bent crystal with a radius greater than the critical radius and an incoming angle lower than the critical angle undergo the channeling effect, which was used to **deflect particles from GeVs up to TeVs energies**.
2. The deflection efficiency is not constant and varies with the particle charge: for **negative particles** is **strongly limited**, while **positive particles** have **optimal deflection efficiency** at high-energy.

Due to the beam-splitting capability, channeling can be used to **measure the positron to electron ratio** of a fraction of particles in astrophysics experiments that do not involve the use of a magnet. In fact, a bent crystal, e.g. Si or Ge, for deflection via channeling would be a **non-cryogenic passive device**, i.e., with no energy consumption.



# Frontier Detectors for Frontier Physics

14<sup>th</sup> Pisa meeting on  
advanced detectors

La Biodola • Isola d'Elba • Italy  
27 May - 2 June, 2018



## THANK YOU FOR THE ATTENTION

bagli@fe.infn.it  
vincenzo.guidi@unife.it  
alexander.howard@cern.ch

